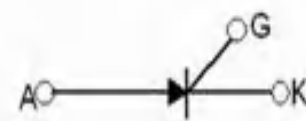




MCR100 - 6/8 Plastic-Encapsulate Thyristors

Silicon Controlled Rectifier



FEATURES

Current- I_{GT} : 200 μ A

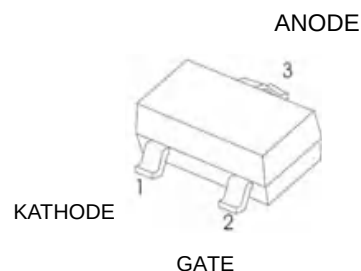
I_{TRMS} : 0.8 A

V_{RRM}/V_{DRM} : MCR100-6: 400 V

MCR100-8: 600 V

Operating and storage junction temperature range

T_J, T_{stg} : -55°C to +150°C



SOT-23

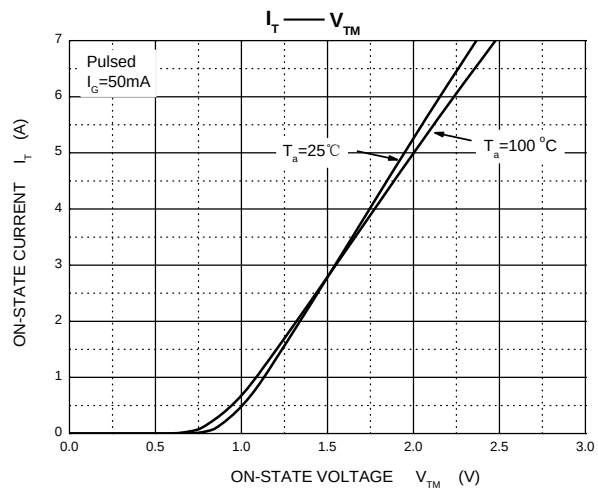
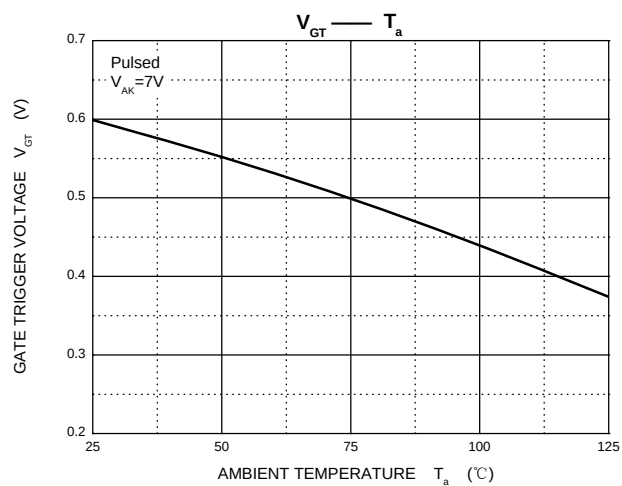
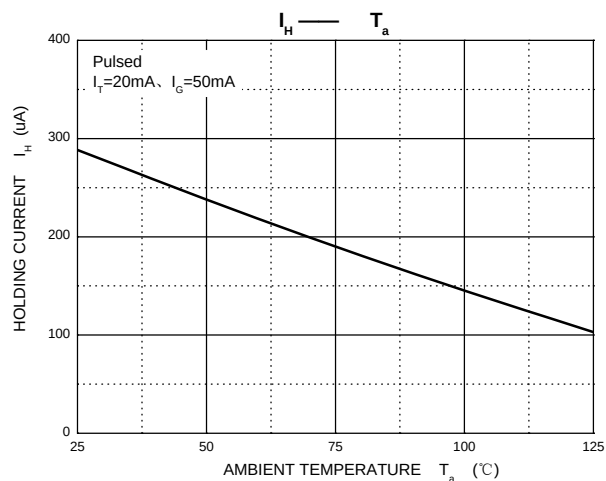
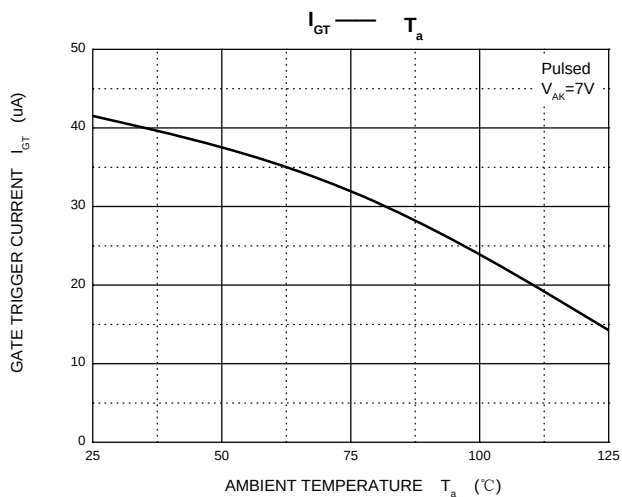
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
On state voltage	V_{TM}^*	$I_{TM}=1A$		1.7	V
Gate trigger voltage	V_{GT}	$V_{AK}=7V$		0.8	V
Peak Repetitive forward and reverse blocking voltage MCR100-6 MCR100-8	V_{DRM} AND V_{RRM}	$I_{DRM}=100\mu A$	400 600		V
Peak forward or reverse blocking Current	I_{DRM} I_{RRM}	V_{AK} = Rated V_{DRM} or V_{RRM}		10	μA
Holding current	I_H	$I_{HL}=20mA, V_{AK}=7V$		5	mA
Gate trigger current	I_{GT}	$V_{AK}=7V$	5	15	μA
			15	30	μA
			30	80	μA
			80	200	μA

* Forward current applied for 1 ms maximum duration, duty cycle $\leq 1\%$.



Typical Characteristics

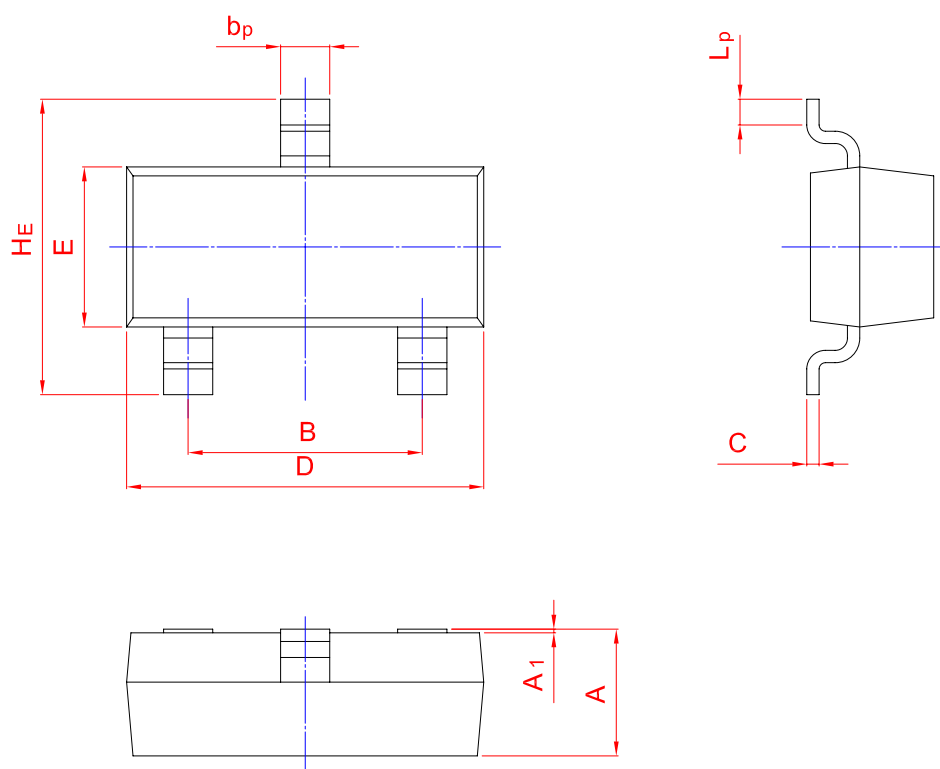




PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b_p	C	D	E	H_E	A_1	L_p
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20